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PROCESSED 27 DEC 2001

214810US-0PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
YASUTAKA ITO ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: 09/926,296 :
FILED: 09 October 2001 :
FOR: CERAMIC SUBSTRATE FOR :
A SEMICONDUCTOR-
PRODUCING/EXAMINING
DEVICE

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application as follows.

IN THE CLAIMS

Please amend the claims as shown on the marked-up copy following this amendment to read as follows.

4. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 1,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

5. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 1,

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wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

6. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 1,

wherein said conductor is formed in a region up to the position of 60% in a thickness-direction from the face opposite to a wafer treating face of said ceramic substrate.

10. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein a conductor is formed on the face opposite to a wafer treating face.

11. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

12. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to claim 7,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

REMARKS

Claims 1-12 are active in the present application. Claims 4-6 and 10-12 have been amended to remove multiple dependencies. No new matter is added. An action on the merits and allowance of claims is solicited.

Respectfully submitted,

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IN THE CLAIMS

--4. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 3] claim 1,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

5. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 4] claim 1,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

6. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 5] claim 1,

wherein said conductor is formed in a region up to the position of 60% in a thickness-direction from the face opposite to a wafer treating face of said ceramic substrate.

10. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 9] claim 7,

wherein a conductor is formed on the face opposite to a wafer treating face.

11. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 10] claim 7,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

12. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 11] claim 7,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.--